L Number	Hits	Search Text	DB	Time stamp
-	155637	polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:43
-	656558	stress$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 09:04
-	3947590	anneal$4 or heat$4 or thermal$3 adj3 treat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:48
-	878976	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:45
-	718828	oxidi$5 or oxidat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 11:33
-	30152	(oxidi$5 or oxidat$5) same (polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 09:10
-	114339	stress$4 same (anneal$4 or heat$4 or thermal$3 adj3 treat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 09:10
-	956	((oxidi$5 or oxidat$5) same (polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon))) and (stress$4 same (anneal$4 or heat$4 or thermal$3 adj3 treat$5)) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 09:12
-	2478932	tungsten or w	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:57
-	643	(((oxidi$5 or oxidat$5) same (polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon))) and (stress$4 same (anneal$4 or heat$4 or thermal$3 adj3 treat$5)) and gate) and (tungsten or w)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 09:24
-	19778	gate with stack$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 09:26
-	182	((oxidi$5 or oxidat$5) same (polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon))) and (stress$4 same (anneal$4 or heat$4 or thermal$3 adj3 treat$5)) and (gate with stack$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 11:32
-	2513	438/585.ccls. or 438/592.ccls. or 438/595.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 10:06
-	546619	defect or trap	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 11:32

-	6508889	suppress$4 or reduc$4 or decreas$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 11:34
-	720568	oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:43
-	7352191	suppress$4 or reduc$4 or decreas$4 or releas$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 11:34
-	50316	(anneal$4 or heat$4 or thermal$3 adj3 treat$5) same (suppress$4 or reduc$4 or decreas$4 or releas$5) same (oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 11:37
-	30328	(oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5) same (polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 11:37
-	1857	((anneal$4 or heat$4 or thermal$3 adj3 treat$5) same (suppress$4 or reduc$4 or decreas$4 or releas$5) same (oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5)) and ((oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5) same (polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon))) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 11:37
-	720568	oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:51
-	155637	polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:45
-	878976	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:46
-	1523136	oxide or dioxide or "sio.sub.2" or "sio.sub2."	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:47
-	2738813	sidewall or side adj2 wall or edge	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:48
-	3947590	anneal$4 or heat$4 or thermal$3 adj3 treat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:49
-	30115	(oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5) near10 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:51

-	35576	(oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:53
-	9036	((oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5) near10 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate)) and ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:54
-	3276	((oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5) near10 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate)) same ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:56
-	512	(((oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5) near10 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate)) same ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))) same (anneal$4 or heat$4 or thermal$3 adj3 treat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:56
-	2478932	tungsten or w	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:57
-	11519	(polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) same gate same (tungsten or w)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 13:58
-	141	((((oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5) near10 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate)) same ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))) same (anneal$4 or heat$4 or thermal$3 adj3 treat$5)) and ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) same gate same (tungsten or w))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:50
-	141	(((((oxidi$5 or oxidat$5 or reoxidi$5 or reoxidat$5) near10 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate)) same ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near10 (sidewall or side adj2 wall or edge))) same (anneal$4 or heat$4 or thermal$3 adj3 treat$5)) and ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) same gate same (tungsten or w))) and (anneal$4 or heat$4 or thermal$3 adj3 treat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:21
-	8935	selectivi$4 near3 (oxidi$5 or oxidat$5) or reoxidi$5 or reoxidat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:53
-	635	(selectivi$4 near3 (oxidi$5 or oxidat$5) or reoxidi$5 or reoxidat$5) near15 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:55

-	19977	(oxide or dioxide or "sio.sub.2" or "sio.sub2.") near20 ((sidewall or side adj2 wall or edge) or side adj2 surface) near20 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:59
-	116	((selectivi$4 near3 (oxidi$5 or oxidat$5) or reoxidi$5 or reoxidat$5) near15 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate)) same ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near20 ((sidewall or side adj2 wall or edge) or side adj2 surface) near20 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 14:59
-	78	(((selectivi$4 near3 (oxidi$5 or oxidat$5) or reoxidi$5 or reoxidat$5) near15 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate)) same ((oxide or dioxide or "sio.sub.2" or "sio.sub2.") near20 ((sidewall or side adj2 wall or edge) or side adj2 surface) near20 ((polysi or polysilicon or (poly or polycrystal$5) adj (si or silicon)) or gate))) and (anneal$4 or heat$4 or thermal$3 adj3 treat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 15:48
-	1105	438/592.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/10 15:49